

In re Appln. of IKEMATSU et al.
Application No. Unassigned

ABSTRACT AMENDMENTS

Replace the Abstract with:

A gate insulating film is formed on a substrate, and electrode-constituting films ~~3, 4,~~ ~~5,~~ and ~~6~~ for constituting a gate electrode are sequentially formed. A silicon nitride film and a second polysilicon film are formed on the metal film, and a resist pattern is formed on the metal film. The second polysilicon film is patterned using the resist pattern as a mask, and the silicon nitride film and the electrode-constituting films are patterned using ~~a~~ the patterned second polysilicon film as a mask. An interlayer insulating film is formed ~~on the entire surface~~ over all of the substrate, and contact holes are formed in the interlayer insulating film. After forming a polysilicon film in the contact holes, polysilicon plugs are formed and the mask is removed by ~~CMP~~ chemical mechanical polishing, using the silicon nitride film as a stopper film.